

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

107 573 822

IAP5 Rec'd PCT/PTO 28 MAR 2006

In re the Application of

Ryoji HOSHI et al.

Application No.: New U.S. National Stage of PCT/JP2004/015395

Filed: March 28, 2006

Docket No.: 127516

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

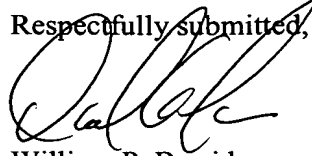
- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 6-9.
- ☒ 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 1-6.
- ☒ 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- ☒ 5. An English language Abstract of one or more non-English language reference is attached hereto. See References 2-8.
- ☒ 6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 2-8.

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☒ 7. Reference 1 corresponds to Reference 5.

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Respectfully submitted,



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WPB:DAT/nxy

Date: March 28, 2006

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Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 127516 <div style="font-size: 24pt; font-weight: bold; text-align: center;">10/ 573 822</div>		APPLICATION NO. New U.S. National Stage of PCT/JP2004/015395	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Ryoji HOSHI et al.			
				FILING DATE March 28, 2006			

U.S. PATENT DOCUMENTS				
Examiner Initials	Cite No.	Document Number	Date	Name
	1.	US 2002/0017234 A1	02/14/2002	ONO et al.

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation
	2.	JP-A-07-223893	08/22/1995	JAPAN	X	X
	3.	JP-A-08-157293	06/18/1996	JAPAN	X	X
	4.	JP-A-11-043397	02/16/1999	JAPAN	X	X
	5.	JP-A-2002-012498	01/15/2002	JAPAN	X	X
	6.	JP-A-2002-226296	08/14/2002	JAPAN	X	X
	7.	JP-A-08-330316	12/13/1996	JAPAN	X	X
	8.	JP-A-11-079889	03/23/1999	JAPAN	X	X

OTHER DOCUMENTS		
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)
	9.	D.T.J. HURLE et al.; "Mechanism of Swirl Defects Formation in Silicon"; <i>Journal of Crystal Growth</i> ; Vol. 59; 1982; pp. 625-643.

EXAMINER	DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date: March 28, 2006